

NPN HIGH POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/371

Devices

2N3902

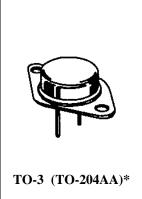
2N5157

Qualified Level

JAN JANTX

MAXIMUM RATINGS

Ratings	Symbol	2N3902	2N5157	Unit
Collector-Emitter Voltage	V _{CEO}	400	500	Vdc
Emitter-Base Voltage	V _{EBO}	5.0	6.0	Vdc
Collector-Base Voltage	V _{CBO}	70	00	Vdc
Base Current	IB	2	.0	Adc
Collector Current	I _C	3	.5	Adc
Total Power Dissipation	р	5	.0	W
@ $T_C = +75^0 C^{(2)}$	P _T	10	00	W
Operating & Storage Temperature Range	T _j , T _{stg}	-65 to	+200	⁰ C
THERMAL CHARACTERISTICS				
Characteristics	Symbol	M	ax.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.	25	⁰ C/W
1) Derate linearly 29 mW/ 0 C for T ₄ > $\pm 25^{0}$ C				



1) Derate linearly 29 mW/ $^{\circ}$ C for T_A > +25 $^{\circ}$ C

2) Derate linearly 0.8 mW/ 0 C for T_C > +75 0 C

*See Appendix A for Package Outline

ELECTRICAL CHARACTERISTICS

Characteris	tics	Symbol	Min.	Max.	Unit
OFF CHARACTERISTICS					
Collector-Emitter Cutoff Current					
$V_{CE} = 325 \text{ Vdc}$	2N3902	I _{CEO}		250	μAdc
$V_{CE} = 400 \text{ Vdc}$	2N5157			250	
Collector-Emitter Cutoff Current		I		500	μAdc
$V_{BE} = 1.5 \text{ Vdc}; V_{CE} = 700 \text{ Vdc}$		I _{CEX}		500	μΑασ
Emitter-Base Cutoff Current					
$V_{EB} = 5.0 \text{ Vdc}$	2N3902	I_{EBO}		200	μAdc
$V_{EB} = 6.0 \text{ Vdc}$	2N5157			200	
ON CHARACTERISTICS ⁽³⁾					
Base-Emitter Saturation Voltage					
$I_{C} = 1.0 \text{ Adc}; I_{B} = 0.1 \text{ Adc}$		V _{BE(sat)}		1.5	Vdc
$I_{\rm C} = 3.5 \text{ Adc}; I_{\rm B} = 0.7 \text{ Adc}$				2.0	
Collector-Emitter Saturation Voltage					
$I_{\rm C} = 1.0 \text{ Adc}; I_{\rm B} = 0.1 \text{ Adc}$		V _{CE(sat)}		0.8	Vdc
$I_{\rm C} = 3.5 \text{ Adc}; I_{\rm B} = 0.7 \text{ Adc}$				2.5	
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2N3902, 2N5157 JAN SERIES

ELECTRICAL CHARACTERISTICS (con't)

Characteristics		Symbol	Min.	Max.	Unit
ON CHARACTERISTICS ⁽³⁾ (con't)					
Forward-Current Transfer Ratio					
$I_{C} = 0.5 \text{ Adc}; V_{CE} = 5.0 \text{ Vdc}$			25		
$I_{C} = 1.0 \text{ Adc}; V_{CE} = 5.0 \text{ Vdc}$		h _{FE}	30	90	
$I_{C} = 2.5 \text{ Adc}; V_{CE} = 5.0 \text{ Vdc}$			10		
$I_{C} = 3.5 \text{ Adc}; V_{CE} = 5.0 \text{ Vdc}$			5		
Collector-Emitter Sustaining Voltage					
$I_{\rm C} = 100 \text{ mAdc}$	2N3902	V _{CEO(sus)}		325	Vdc
C	2N5157	020(845)		400	
OYNAMIC CHARACTERISTICS					
Small-Signal Short-Circuit Forward Currer	nt Transfer Ratio	1, 1	2.5	25	
$I_{C} = 0.2$ Adc; $V_{CE} = 10$ Vdc, $f = 1$ MHz		h _{fe}	2.5	25	
Output Capacitance		G		250	г
$V_{CB} = 10$ Vdc; $I_E = 0$, 100 kHz $\le f \le 1.0$	MHz	C _{obo}		250	pF
SWITCHING CHARACTERISTICS					
Turn-On Time		t		0.0	
$V_{CC} = 125 \text{ Vdc}; I_C = 1.0 \text{ Adc}; I_{B1} = 0.1 \text{ Adc}$	dc	ton		0.8	μs
Turn-Off Time		t cc		17	
$V_{CC} = 125 \text{ Vdc}; I_C = 1.0 \text{ Adc}; I_{B1} = 0.1 \text{ Adc}$	Adc; $-I_{B2} = 0.50$ Adc	toff		1.7	μs
SAFE OPERATING AREA		·			
DC Tests (continuous)					
$T_{C} = +25^{0}C$; t ≥ 1.0 s (See Figure 3 of M	IL-PRF-19500/371)				
Test 1					
$V_{CE} = 28.6$ Vdc, $I_C = 3.5$ Adc					
Test 2					
$V_{CE} = 70$ Vdc, $I_{C} = 1.43$ Adc					
Test 3					
$V_{CE} = 325$ Vdc, $I_C = 55$ mAdc	2N3902				
$V_{CE} = 400$ Vdc, $I_C = 35$ mAdc	2N5157				
Switching Tests	21(3137				
Load condition C (unclamped inductiv	e load)				
$T_{\rm C} = 25^{\circ}$ C; duty cycle $\leq 10\%$; R _S = 0.1 Ω		F-19500/371)			
Test 1	(~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~				
$t_P =$ approximately 3 ms (vary to obtain I ₀	The result is the result of t	Vdc: $R_{PP2} = 3 k\Omega$:			
$V_{BB2} = 1.5 \text{ Vdc}; V_{CC} = 50 \text{ Vdc}; I_C = 3.5 \text{ J}$					
$T_{BB2} = 1.5$ (ac, $T_{C} = 5.0$ (ac, $T_{C} = 5.5$)	100, 12 = 00 mm, 10 = 0 m, 100				
$t_P =$ approximately 3 ms (vary to obtain I _C)	$R_{RP1} = 100 \Omega \cdot V_{PP1} = 100$	$Vdc \cdot R_{PP2} = 3 kQ \cdot$			
$V_{BB2} = 1.5$ Vdc; $I_C = 0.6$ Adc $V_{CC} = 50$ V					
Switching Tests	dc, L = 200 mm, R = 0.32, 100 mm	$\mathbf{R}_{\mathrm{L}} = 0.322$			
Load condition (clamped inductive loa	d)				
$T_{\rm C} = +25^{0}$ C; duty cycle $\le 10\%$. (See Fi		(371)			
Test 1 (300 J)		/			
$t_{\rm P}$ = approximately 30 ms (vary to obtain	I_{\odot} : $R_{s} = 0.1 \Omega$: $R_{PP1} = 20$	Ω : V _{BB1} = 10 Vdc [·] H	$R_{BB2} = 100.9$	<u>.</u>	
$V_{BB2} = 1.5 \text{ Vdc}; V_{CC} = 50 \text{ Vdc}; I_C = 3.5 \text{ J}$			-002 1001	,	
(A suitable clamping circuit or diode can		L - V==-			
Clamp Voltage = $400 + 0$, -5 Vdc	2N3902				
Clamp Voltage = $500 + 0$, -5 Vdc	2N5902 2N5157				
(Clamped voltage must be reached)					
S.) Pulse Test: Pulse Width = 300μ s, Duty C	vcle $\leq 2.0\%$.				
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